

/ Descriptions

SOT-23 PNP Silicon PNP transistor in a SOT-23 Plastic Package.

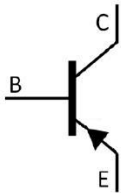
/ Features

Low current, high voltage.

/ Applications

Telephony and professional communication equipment.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2 Emitter PIN 3 Collector

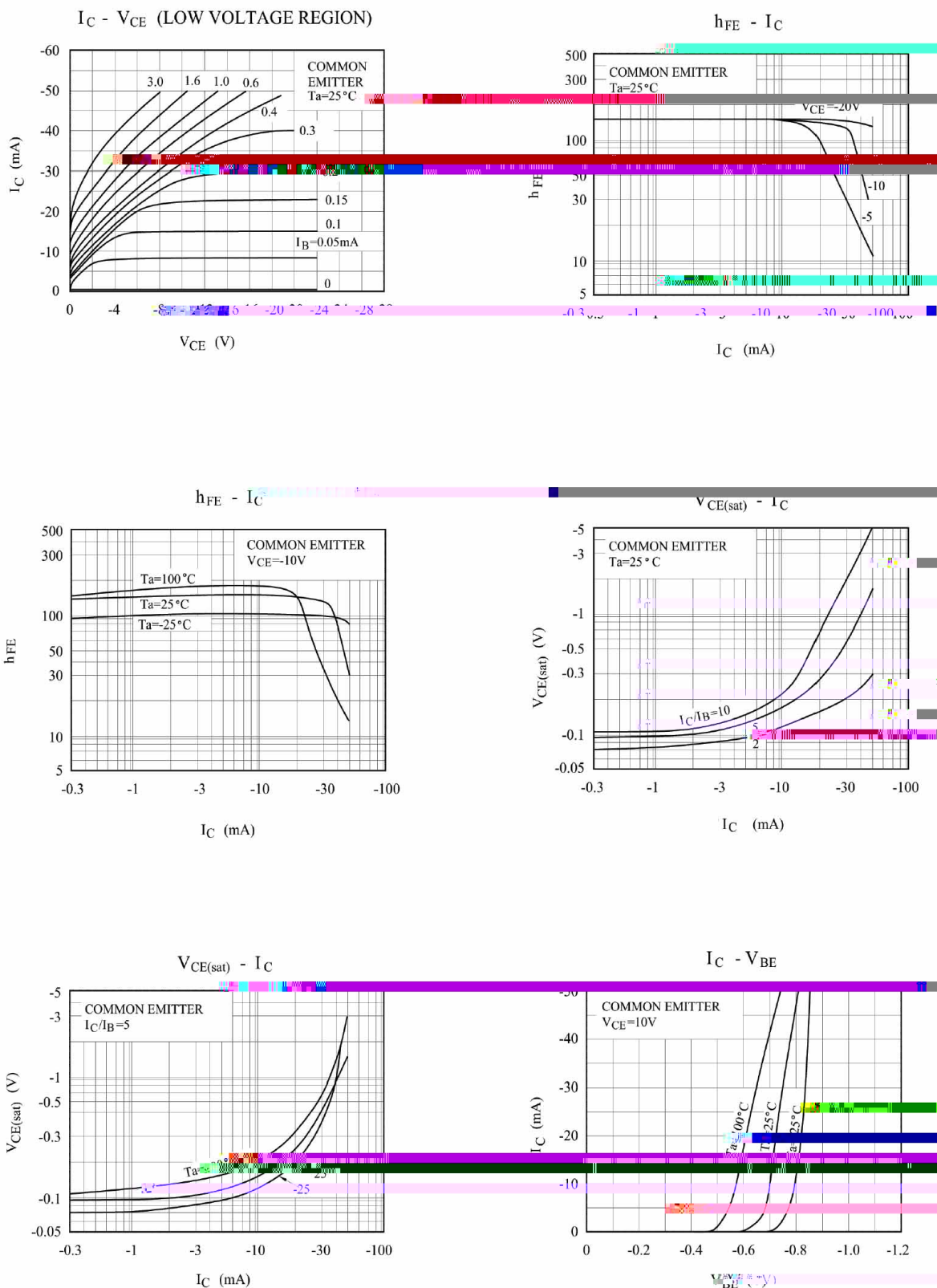
/ h_{FE} Classifications & Marking

h_{FE} Range	>50
Marking	H1W

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-300	V
Collector to Emitter Voltage	V_{CEO}	-300	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-50	mA
Peak Collector Current - Continuous	I_{CM}	-100	mA
Base Current	I_B	-50	mA
Collector Power Dissipation	P_C	250	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBR}	$I_C = -100\mu A, I_B = 0$	-300			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C = -1.0mA, I_B = 0$	-300			V

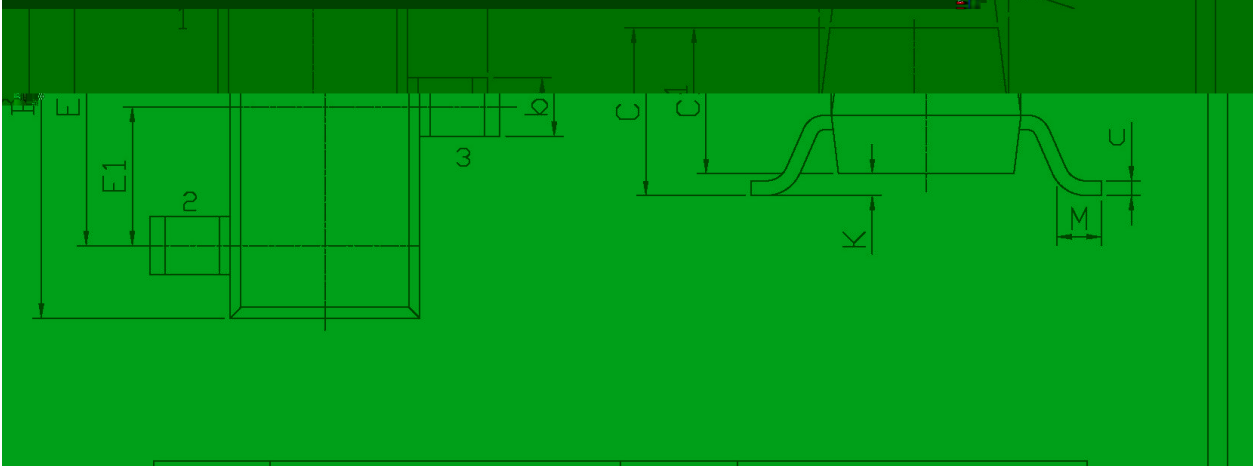
/ Electrical Characteristic Curve



/ Package Dimensions

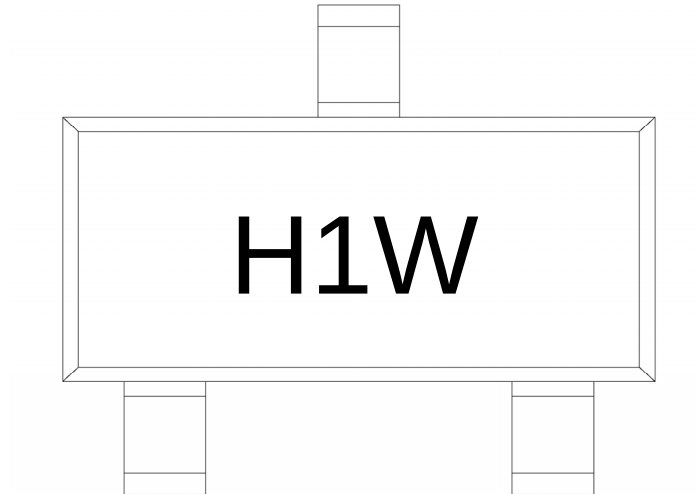
SOT-23

单位: mm



Symbol	Dimensions in Millimeters		Symbol	Dimensions in Millimeters	
	Min	Max		Min	Max
L	2.2	2.7	C	1.30Max	
L1	0.45	0.65	C1	0.90	1.20
A	1.15	1.50	c	0.05	0.20
B	2.70	3.40	K	0	0.10
E	1.70	2.10	M	0.20MIN	
E1	0.85	1.05	P	7°	
b	0.35	0.55			

/ M a r k i n g I n s t r u c t i o n s



H

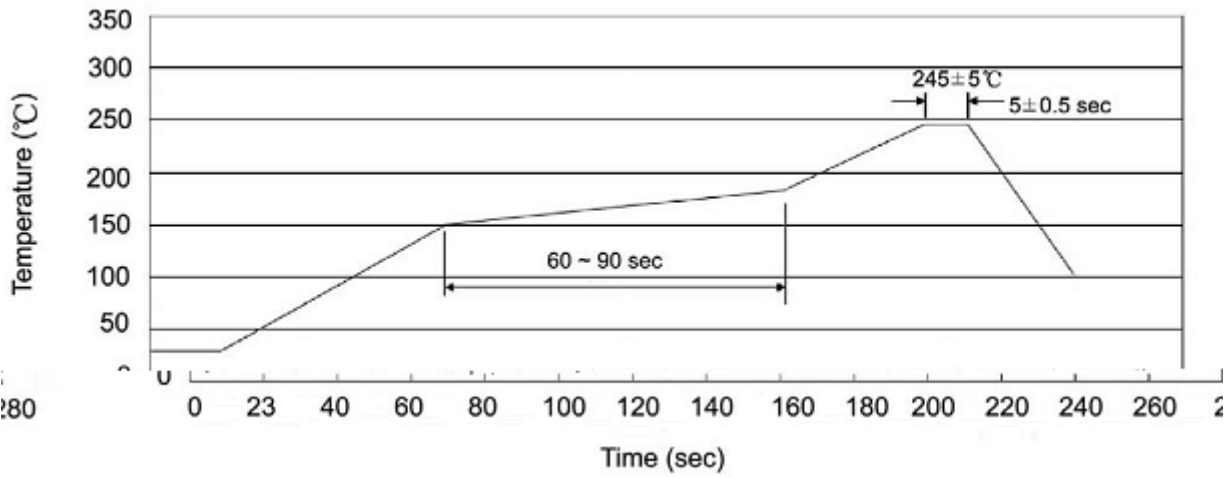
1W

Note:

H: Company Code.

1W: Product Type Code.

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Note:

- 1

25 150

60 90sec;

1.Preheating:25~150 , Time:60~90sec.
- 2

245±5

5±0.5sec;

2.Peak Temp.:245±5 , Duration:5±0.5sec.
- 3

2 10 /sec.

3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

260±5 10±1 sec. Temp.:260±5℃ Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只 卷盘	卷盘 盒	只 盒	盒 箱	只 箱		盒	箱
						"		

/ Notices